

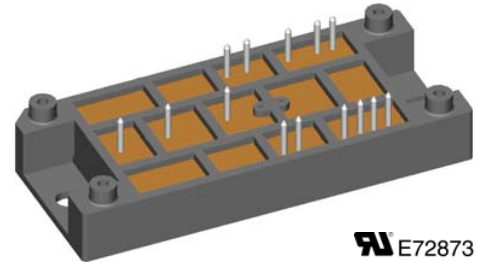
Standard Rectifier Module


3 ~ Rectifier	Brake Chopper
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAVM} = 188 \text{ A}$	$I_{C25} = 155 \text{ A}$
$I_{FSM} = 1100 \text{ A}$	$V_{CE(sat)} = 1.9 \text{ V}$

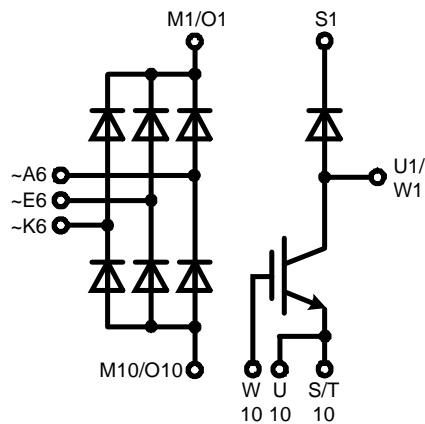
3~ Rectifier Bridge + Brake Unit

Part name

VUB120-16NOX



 E72873



Features / Advantages:

- Soldering connections for PCB mounting
- Convenient package outline

Applications:

- 3~ Rectifier with brake unit for drive inverters

Package:

- Housing: V2-Pack
- DCB ceramic base plate
- Isolation voltage 3600 V~
- Easy to mount with two screws
- Space and weight savings
- RoHS compliant

Rectifier				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage					1700	V	
V_{RRM}	max. repetitive reverse blocking voltage					1600	V	
I_R	reverse current, drain current	$V_{RD} = 1600$ V	$T_{VJ} = 25^\circ\text{C}$			50	μA	
		$V_{RD} = 1600$ V	$T_{VJ} = 125^\circ\text{C}$			2	mA	
V_F	forward voltage drop	$I_T = 60$ A	$T_{VJ} = 25^\circ\text{C}$			1.16	V	
			$T_{VJ} = 25^\circ\text{C}$			1.36	V	
		$I_T = 120$ A	$T_{VJ} = 125^\circ\text{C}$			1.09	V	
			$T_{VJ} = 125^\circ\text{C}$			1.35	V	
$I_{D(AV)M}$	bridge output current	$T_C = 80^\circ\text{C}$ rectangular $d = 1/3$	$T_{VJ} = 150^\circ\text{C}$			188	A	
V_{FO}	threshold voltage	} for power loss calculation only				0.81	V	
r_F	slope resistance							4.4
R_{thJC}	thermal resistance junction to case					0.60	K/W	
R_{thCH}	thermal resistance case to heatsink			0.2			K/W	
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$			200	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine $t = 8,3$ ms; (60 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			1.10	kA	
			$V_R = 0$ V			1.19	kA	
		$t = 10$ ms; (50 Hz), sine $t = 8,3$ ms; (60 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			935	A	
			$V_R = 0$ V			1.01	kA	
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine $t = 8,3$ ms; (60 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			6.05	kA ² s	
			$V_R = 0$ V			5.89	kA ² s	
		$t = 10$ ms; (50 Hz), sine $t = 8,3$ ms; (60 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			4.37	kA ² s	
			$V_R = 0$ V			4.25	kA ² s	
C_J	junction capacitance	$V_R = 400$ V $f = 1$ MHz	$T_{VJ} = 25^\circ\text{C}$		37		pF	

Brake IGBT				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
V_{GES}	max. DC gate voltage				± 20	V	
V_{GEM}	max. transient collector gate voltage				± 30	V	
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			155	A	
I_{C80}		$T_C = 80^{\circ}\text{C}$			107	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			500	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 100\text{A}; V_{GE} = 15\text{V}$		1.9	2.2	V	
				2.5		V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4\text{mA}; V_{GE} = V_{CE}$	5.4	5.9	6.5	V	
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{V}$			0.1	mA	
				0.1		mA	
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{V}; V_{GE} = 15\text{V}; I_C = 100\text{A}$		295		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{V}; I_C = 100\text{A}$ $V_{GE} = \pm 15\text{V}; R_G = 6.8\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$		70	ns	
t_r	current rise time				40	ns	
$t_{d(off)}$	turn-off delay time				250	ns	
t_f	current fall time				100	ns	
E_{on}	turn-on energy per pulse				8.5	mJ	
E_{off}	turn-off energy per pulse				11.5	mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{V}; R_G = 6.8\ \Omega$					
I_{CM}		$V_{CEK} = 1200\text{V}$			300	A	
SCSOA	short circuit safe operating area						
t_{sc}	short circuit duration	$V_{CE} = 720\text{V}; V_{GE} = \pm 15\text{V}$			10	μs	
I_{sc}	short circuit current	$R_G = 6.8\ \Omega$; non-repetitive		400		A	
R_{thJC}	thermal resistance junction to case				0.25	K/W	
R_{thCH}	thermal resistance case to heatsink			0.1		K/W	

Brake Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			62	A	
I_{F80}		$T_C = 80^{\circ}\text{C}$			40	A	
V_F	forward voltage	$I_F = 30\text{A}$		2.71		V	
				1.94		V	
I_R	reverse current	$V_R = V_{RRM}$			0.25	mA	
					1	mA	
Q_{rr}	reverse recovery charge	$V_R = 600\text{V}$ $-di_F/dt = 400\text{A}/\mu\text{s}$ $I_F = 30\text{A}$	$T_{VJ} = 125^{\circ}\text{C}$		1.8	μC	
I_{RM}	max. reverse recovery current				23	A	
t_{rr}	reverse recovery time				150	ns	
R_{thJC}	thermal resistance junction to case				0.9	K/W	
R_{thCH}	thermal resistance case to heatsink			0.3		K/W	

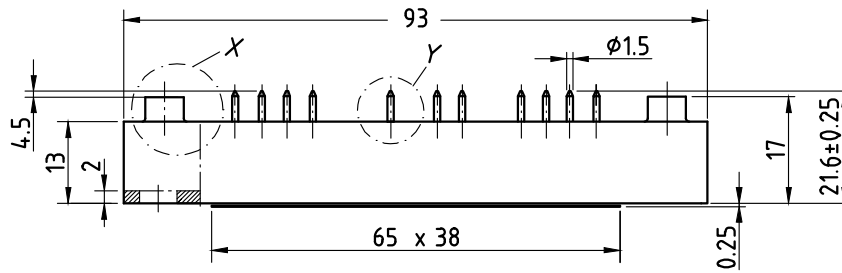
Package V2-Pack			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	I_{RM} current	per terminal			100	A
T_{stg}	storage temperature		-40		125	°C
T_{vj}	virtual junction temperature		-40		150	°C
Weight				76		g
M_D	mounting torque		2		2.5	Nm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm



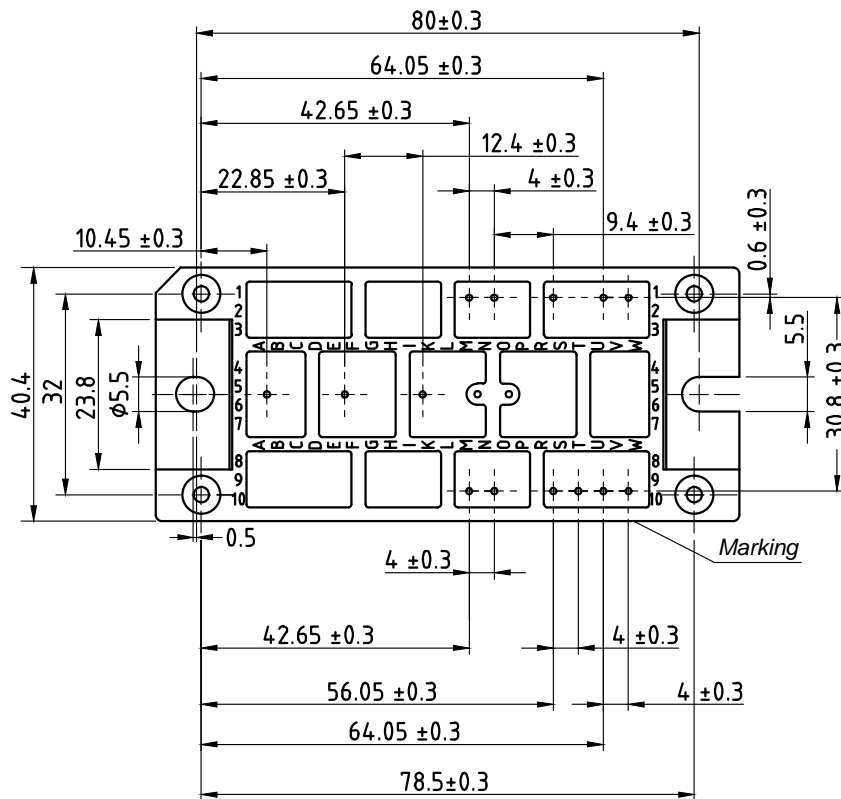
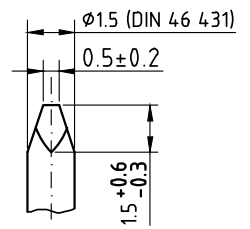
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUB120-16NOX	VUB120-16NOX	Box	6	510468

Similar Part	Package	Voltage class
VUB120-16NOXT	V2-Pack	1600

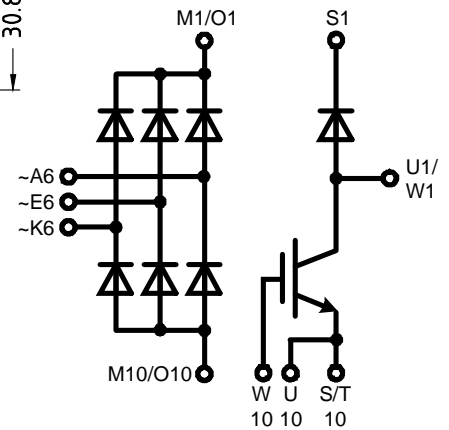
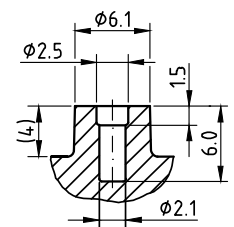
Outlines



Detail Y M 5:1



Detail X M 2:1



Rectifier

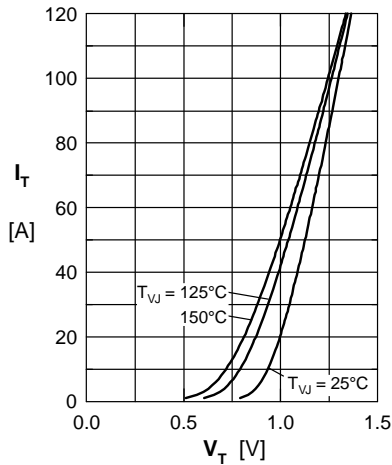


Fig.1 Forward current versus voltage drop per diode

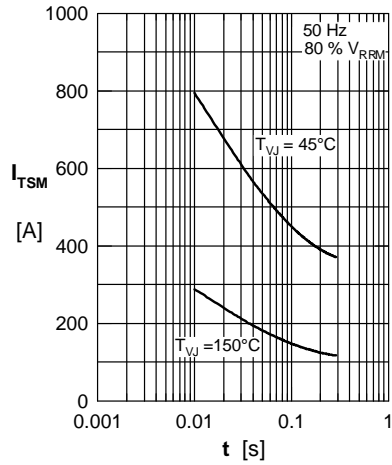


Fig.2 Surge overload current

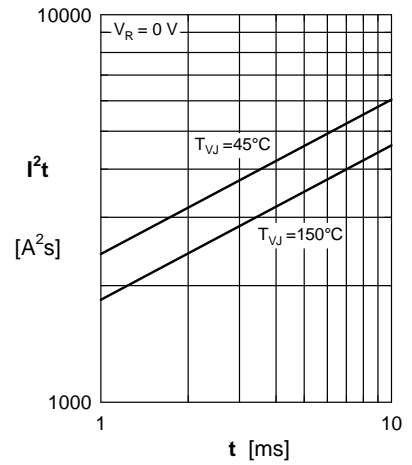


Fig.3 I^2t versus time per diode

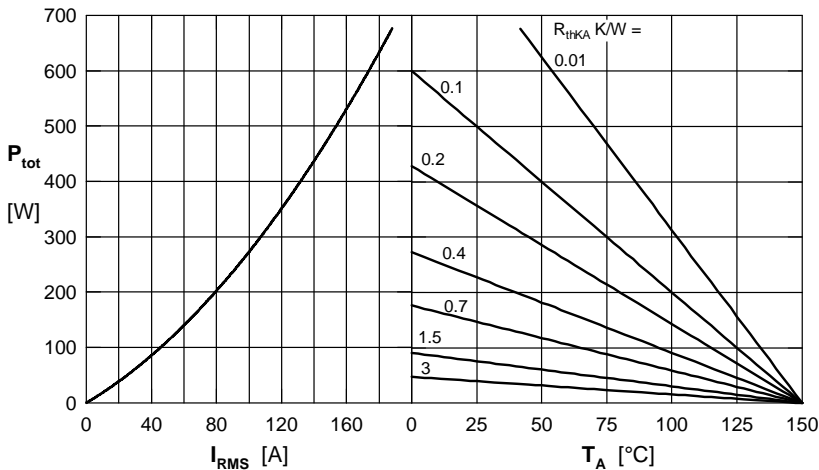


Fig.4 Power dissipation versus direct output current and ambient temperature, sine 180°

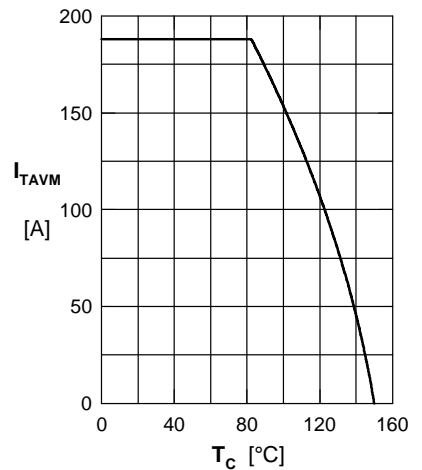


Fig.5 Max. forward current vs. case temperature

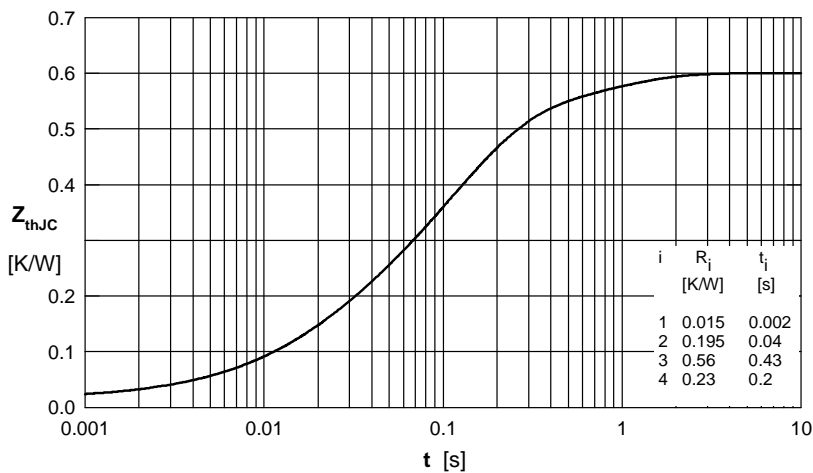


Fig.6 Transient thermal impedance junction to case

Brake IGBT

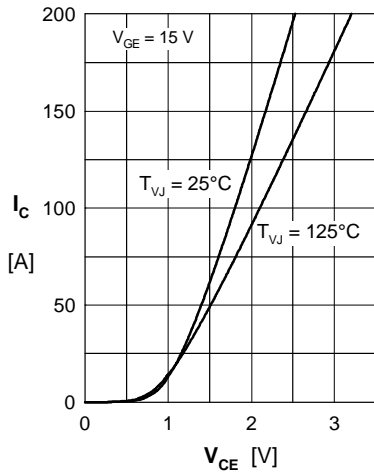


Fig. 1 Typ. output characteristics

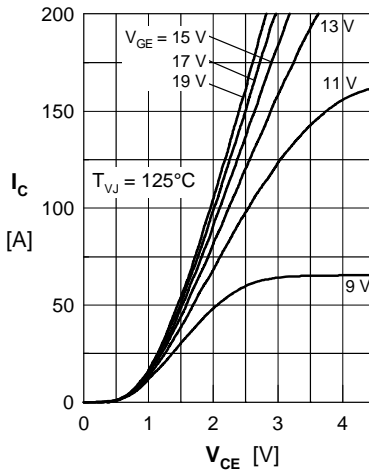


Fig. 2 Typ. output characteristics

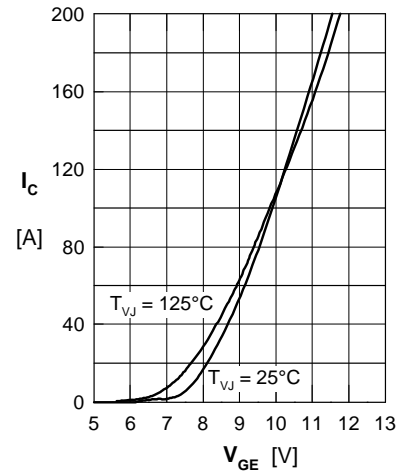


Fig. 3 Typ. transfer characteristics

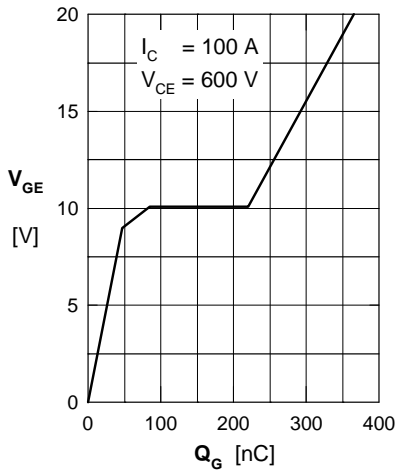


Fig. 4 Typ. turn-on gate charge

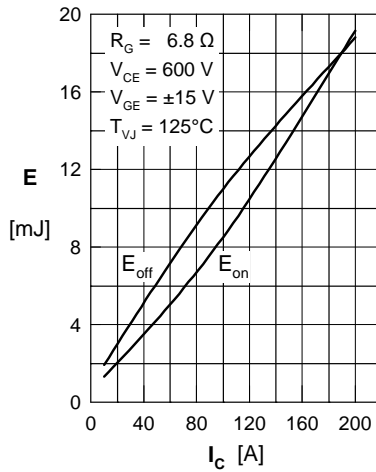


Fig. 5 Typ. switching energy versus collector current

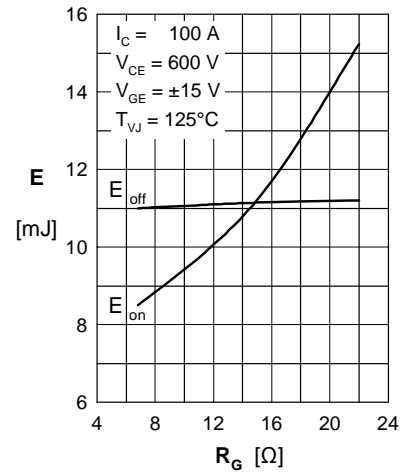


Fig. 6 Typ. switching energy versus gate resistance

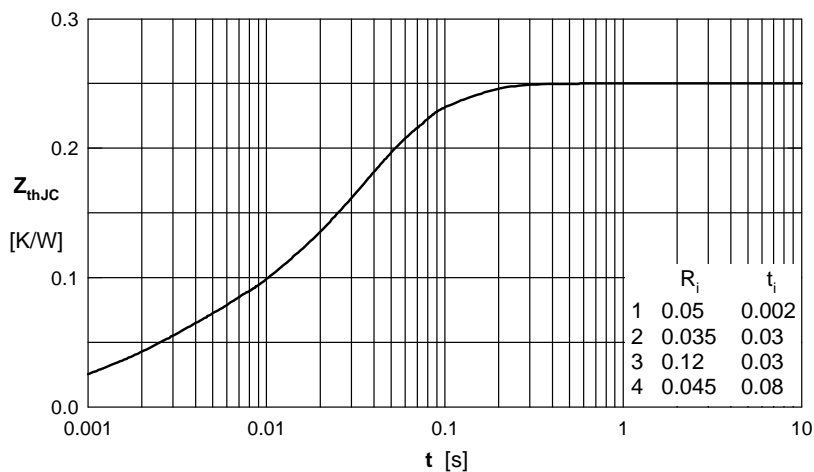


Fig. 7 Transient thermal impedance junction to case

Brake Diode

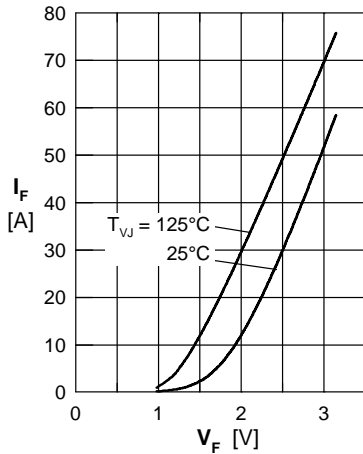


Fig. 1 Typ. forward current I_F vs. V_F

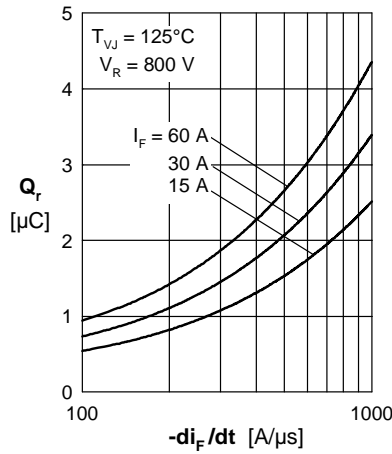


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

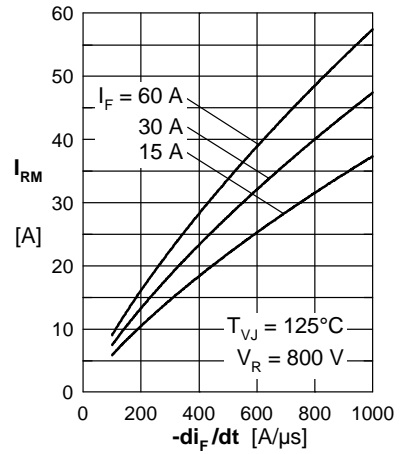


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

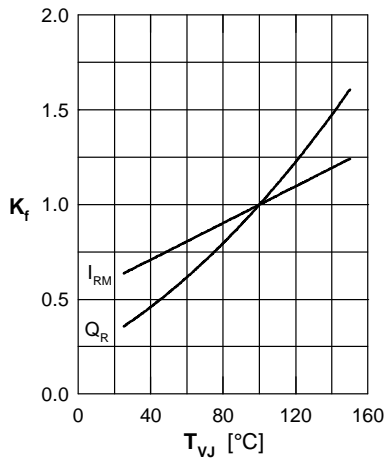


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} , versus T_{VJ}

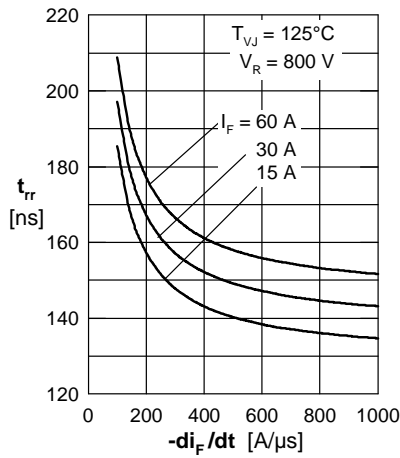


Fig. 5 Typ. recovery time t_{rr} vs. $-di_F/dt$

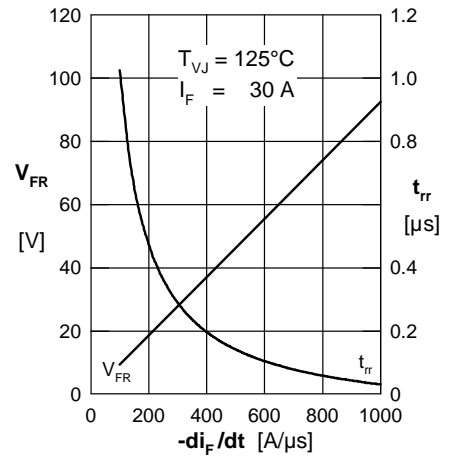


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

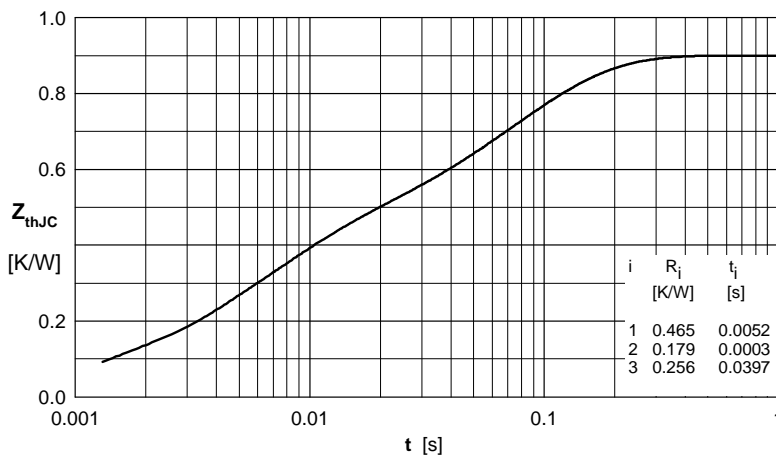


Fig. 7 Typ. transient thermal impedance junction to case